

Super Fast Recovery Diode

RF1501NS3S

●Series

Ultra Fast Recovery

●Applications

General rectification

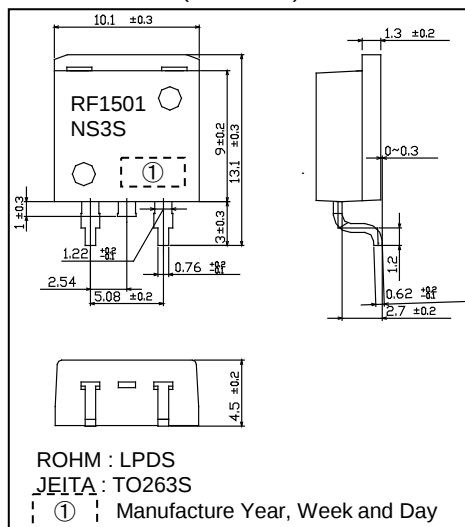
●Features

- 1) Ultra low switching loss
- 2) High current overload capacity

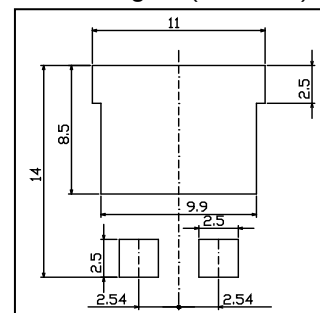
●Construction

Silicon epitaxial planer

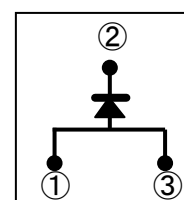
●Dimensions (Unit : mm)



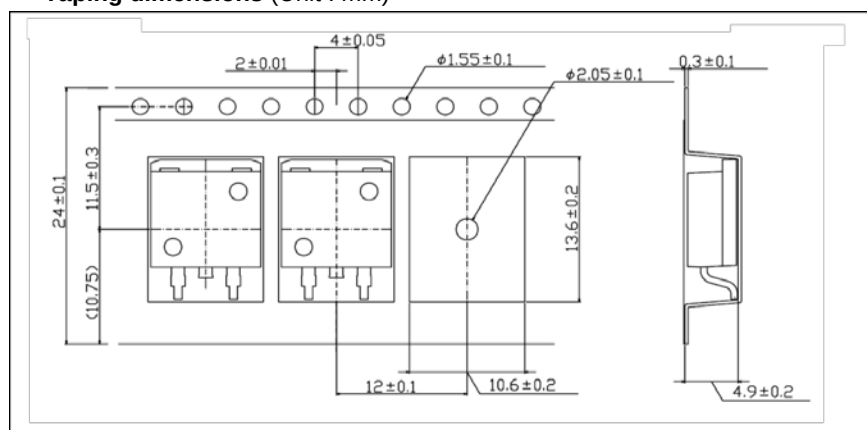
●Land size figure (Unit : mm)



●Structure



●Taping dimensions (Unit : mm)

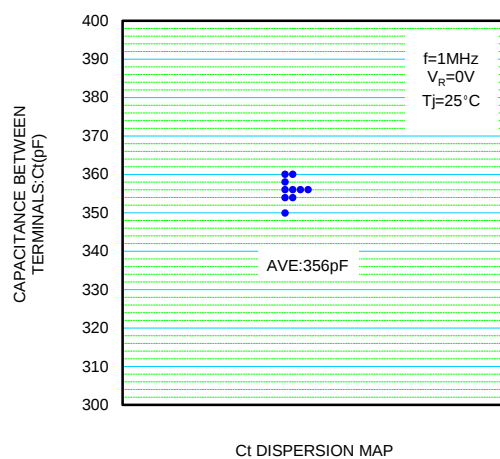
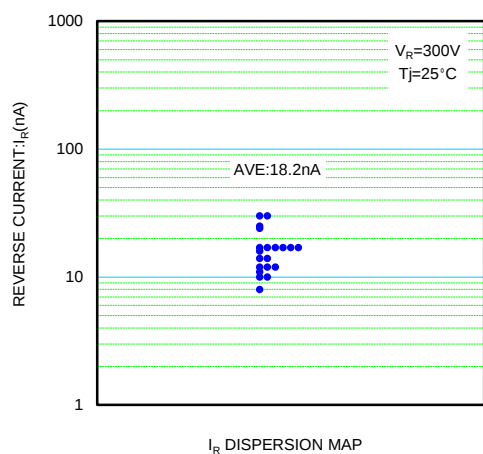
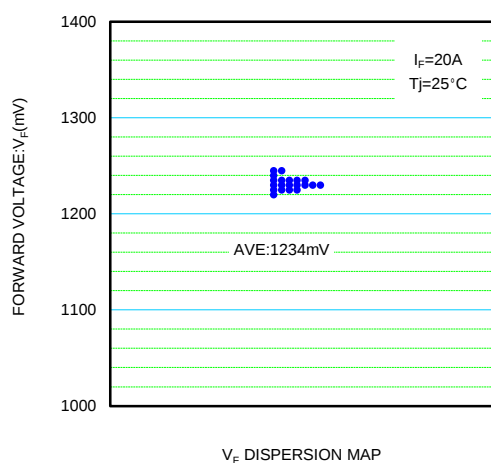
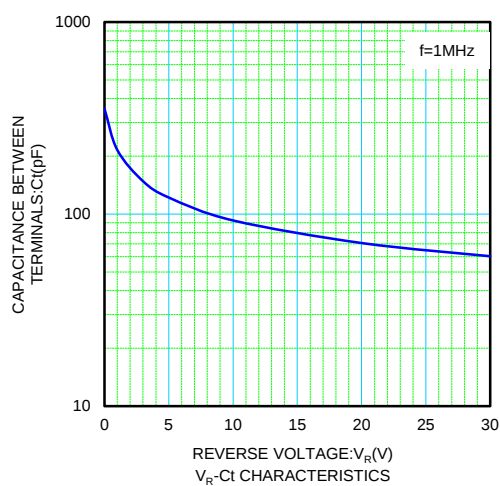
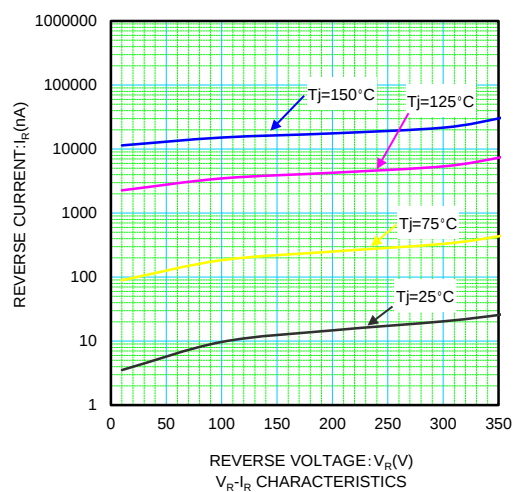
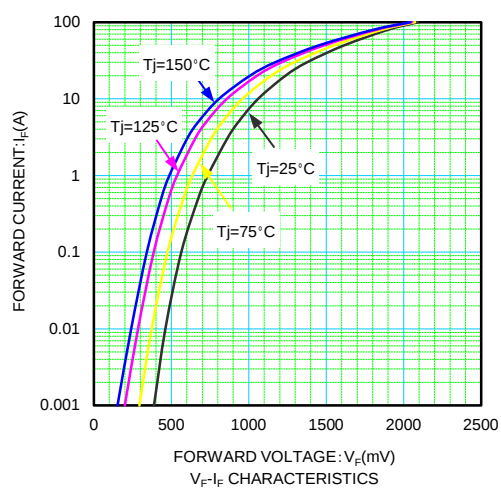


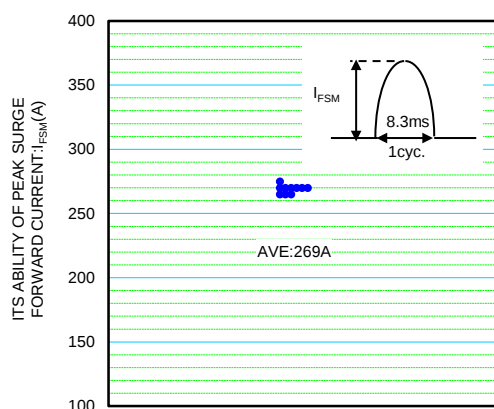
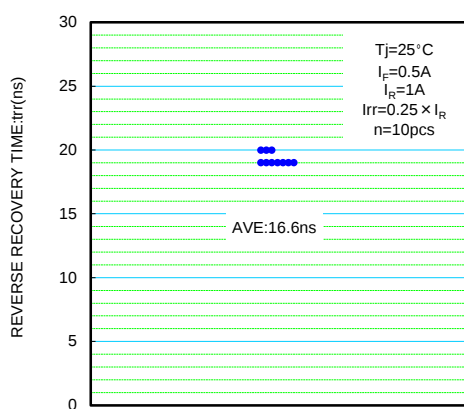
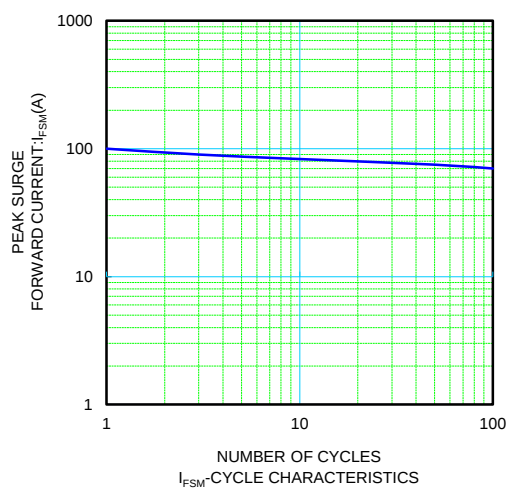
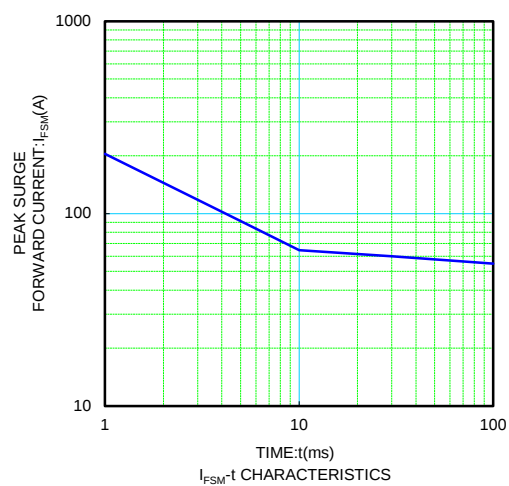
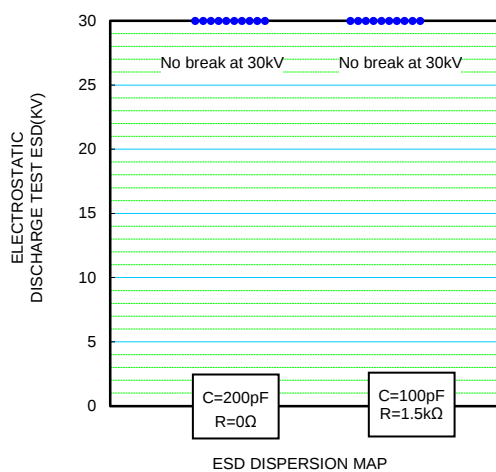
●Absolute maximum ratings (Tc=25°C)

Parameter	Symbol	Conditions	Limits	Unit
Repetitive peak reverse voltage	V_{RM}	Duty ≤ 0.5	350	V
Reverse voltage	V_R	Direct voltage	300	V
Average rectified forward current	I_o	60Hz half sin wave resistive load at Tc=54°C	20	A
Forward current surge peak	I_{FSM}	60Hz half sin wave, Non-repetitive one cycle peak value, Tj=25°C	100	A
Junction temperature	Tj		150	°C
Storage temperature	Tstg		- 55 to +150	°C

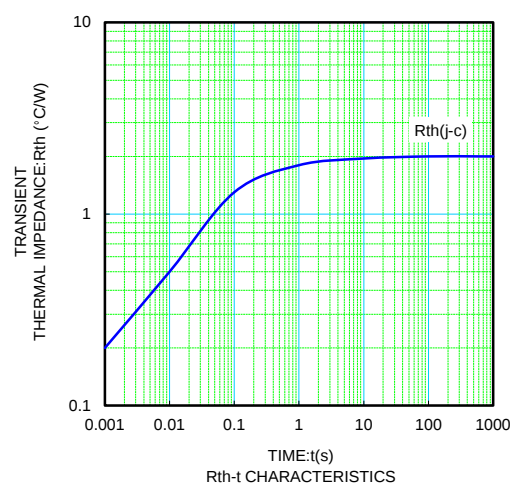
●Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward voltage	V_F	$I_F=20A$	—	1.35	1.5	V
Reverse current	I_R	$V_R=300V$	—	0.06	10	μA
Reverse recovery time	trr	$I_F=0.5A, I_R=1A, I_{rr}=0.25 \times I_R$	—	22	30	ns
Thermal resistance	Rth(j-c)	junction to case	—	—	2.5	°C/W



 I_{FSM} DISPERSION MAP t_{rr} DISPERSION MAP I_{FSM} CYCLE CHARACTERISTICS I_{FSM} - t CHARACTERISTICS

ESD DISPERSION MAP

 R_{th} - t CHARACTERISTICS

